ACT108W-600E

AC Thyristor power switch

Rev. 02 — 26 May 2009

Product data sheet

1. Product profile

1.1 General description

AC Thyristor power switch in a SOT223 surface-mountable plastic package

1.2 Features and benefits

- Common terminal on mounting base enables shared cooling pad
- Exclusive negative gate triggering
- Full cycle AC conduction
- High over-voltage withstand capability

1.3 Applications

- Contactors, circuit breakers, valves, dispensers and door locks
- Fan motor circuits

1.4 Quick reference data

Table 1. Quick reference

- Remote gate separates the gate driver from the effects of the load current
- Surface-mountable plastic package
- Very high noise immunity
- Lower-power highly inductive, resistive and safety loads
- Pump motor circuits

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 112 °C; see <u>Figure 3;</u> see <u>Figure 1;</u> see <u>Figure 2</u>	-	-	0.8	A
I _{GT}	gate trigger current	$V_D = 12 V; T_j = 25 °C;$ $I_T = 100 mA; LD+ G-;$ see <u>Figure 10</u>	1	-	10	mA
		$V_D = 12 \text{ V}; \text{ T}_j = 25 \text{ °C};$ I _T = 100 mA; LD- G-	1	-	10	mA
V _{CL}	clamping voltage	I _{CL} = 100 mA; t _p = 1 ms; T _j ≤ 125 °C; see <u>Figure 17</u>	650	-	-	V
V _{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; see <u>Figure 6</u>	-	-	2	kV
V _T	on-state voltage	I _T = 1.1 A; see <u>Figure 13</u>	-	-	1.3	V



2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	LD	load		
2	СМ	common		
3	G	gate		G-OF
mb	СМ	mounting base; connected to common		
			SOT223 (SC-73)	

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
ACT108W-600E	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

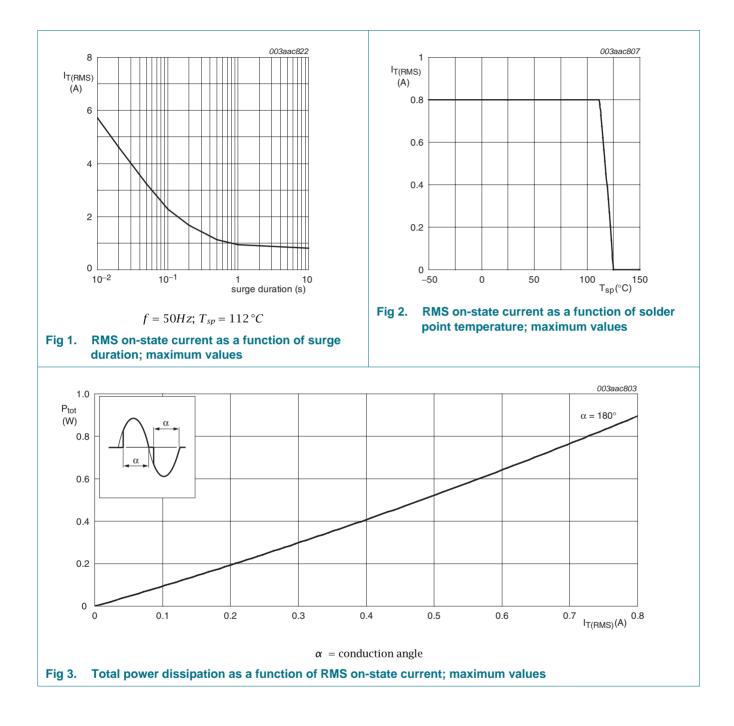
4. Limiting values

Table 4.Limiting values

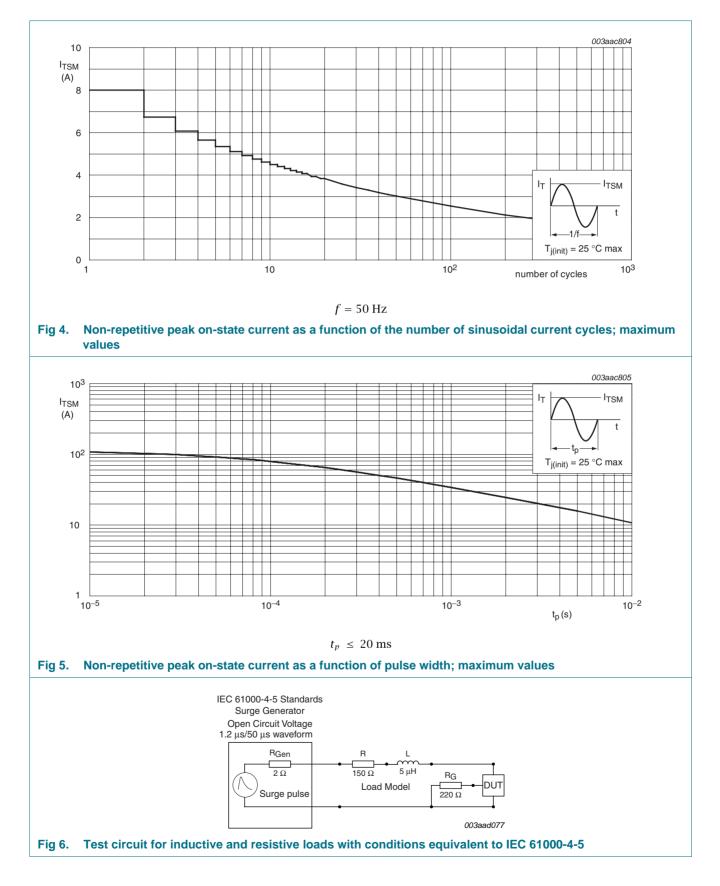
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
repetitive peak off-state voltage		-	600	V
RMS on-state current	full sine wave; T _{sp} ≤ 112 °C; see <u>Figure 3;</u> see <u>Figure 1</u> ; see <u>Figure 2</u>	-	0.8	А
rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 0.2 A/µs	-	100	A/µs
peak gate current	t = 20 µs	-	1	А
peak gate voltage	positive applied gate voltage	-	15	V
storage temperature		-40	150	°C
junction temperature		-	125	°C
non-repetitive peak	full sine wave; $t_p = 16.7 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$	-	8.8	А
on-state current	full sine wave; $t_p = 20 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	8	А
I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.32	A ² s
average gate power	over any 20 ms period	-	0.1	W
peak pulse voltage	$T_j = 25 \text{ °C}; \text{ non-repetitive, off-state; see } \frac{\text{Figure 6}}{1000}$	-	2	kV
	repetitive peak off-state voltage RMS on-state current rate of rise of on-state current peak gate current peak gate voltage storage temperature junction temperature non-repetitive peak on-state current	repetitive peak off-state voltagefull sine wave; $T_{sp} \le 112 \degree C$; see Figure 3; see Figure 1; see Figure 2RMS on-state currentfull sine wave; $T_{sp} \le 112 \degree C$; see Figure 3; see Figure 1; see Figure 2rate of rise of on-state current $I_T = 1 \ A$; $I_G = 20 \ mA$; $dI_G/dt = 0.2 \ A/\mu s$ peak gate current $t = 20 \ \mu s$ peak gate voltagepositive applied gate voltagestorage temperaturejunction temperaturejunction temperaturefull sine wave; $t_p = 16.7 \ ms; T_{j(init)} = 25 \degree C$ non-repetitive peak on-state currentfull sine wave; $t_p = 20 \ ms; T_{j(init)} = 25 \degree C$; see Figure 4; see Figure 5 l^2t for fusing $t_p = 10 \ ms; sine-wave pulse$ average gate powerover any 20 \ ms period	repetitive peak off-state voltage-RMS on-state currentfull sine wave; $T_{sp} \le 112 ^{\circ}C$; see Figure 3; see Figure 1; see Figure 2-rate of rise of on-state current $I_T = 1 A$; $I_G = 20 \text{mA}$; $dI_G/dt = 0.2 A/\mu s$ -peak gate current $t = 20 \mu s$ -peak gate voltagepositive applied gate voltage-storage temperature-40junction temperature-non-repetitive peak on-state currentfull sine wave; $t_p = 16.7 \text{ms}; T_{j(init)} = 25 ^{\circ}C$ - I^2t for fusing $t_p = 10 \text{ms};$ sine-wave pulse- I^2t for fusing $t_p = 10 \text{ms};$ sine-wave pulse-average gate powerover any 20 \text{ms period}-	repetitive peak off-state voltage-600RMS on-state currentfull sine wave; $T_{sp} \le 112 ^{\circ}C$; see Figure 3; see Figure 1; see Figure 2-0.8Rate of rise of on-state current $I_T = 1 A$; $I_G = 20 \text{mA}$; $dI_G/dt = 0.2 \text{A/}\mu\text{s}$ -100peak gate current $I_T = 1 A$; $I_G = 20 \text{mA}$; $dI_G/dt = 0.2 \text{A/}\mu\text{s}$ -1peak gate current $t = 20 \mu\text{s}$ -1peak gate voltagepositive applied gate voltage-15storage temperature-40150junction temperature-125non-repetitive peak on-state currentfull sine wave; $t_p = 16.7 \text{ms}; T_{j(init)} = 25 ^{\circ}\text{C}$; see Figure 4; see Figure 5-8.8 l^2t for fusing $t_p = 10 \text{ms};$ sine-wave pulse-0.32average gate powerover any 20 \text{ms period}-0.1

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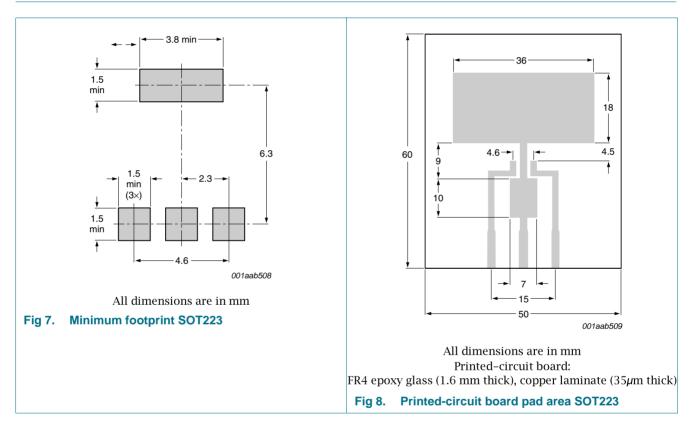


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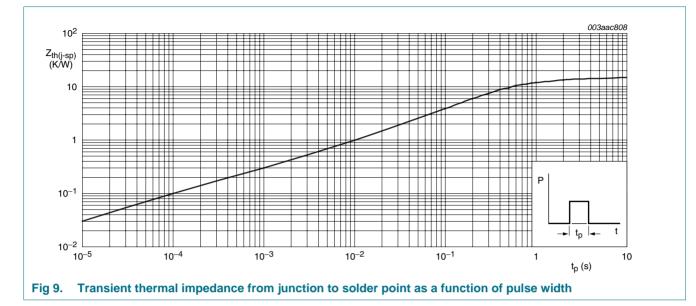
5. Thermal characteristics

Table 5.	Thermal characteristics	5				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}		full cycle with heatsink compound; see <u>Figure 9</u>	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted for minimum footprint; see Figure 7	-	156	-	K/W
		full cycle; printed-circuit board mounted for pad area; see Figure 8	-	70	-	K/W



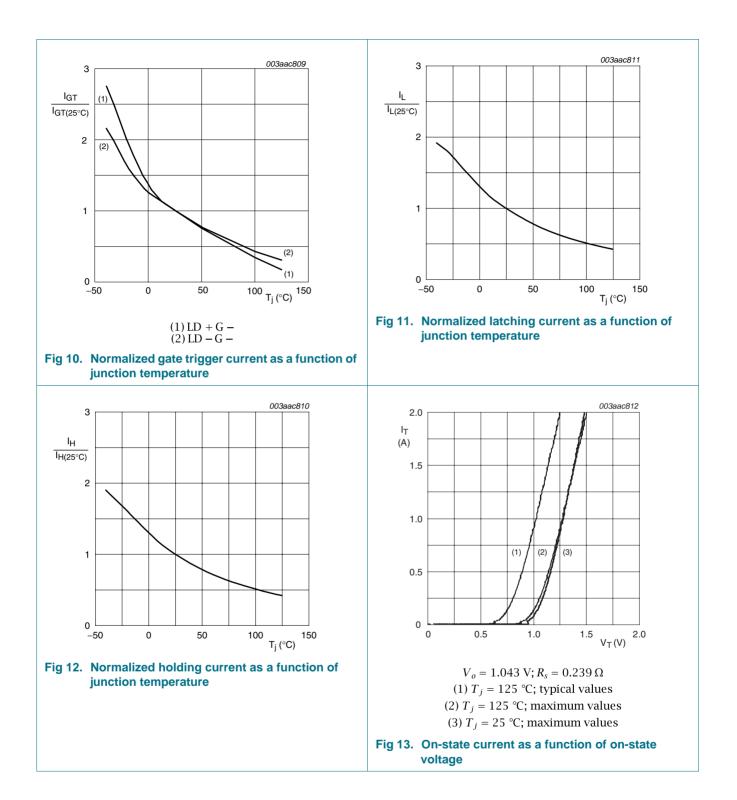
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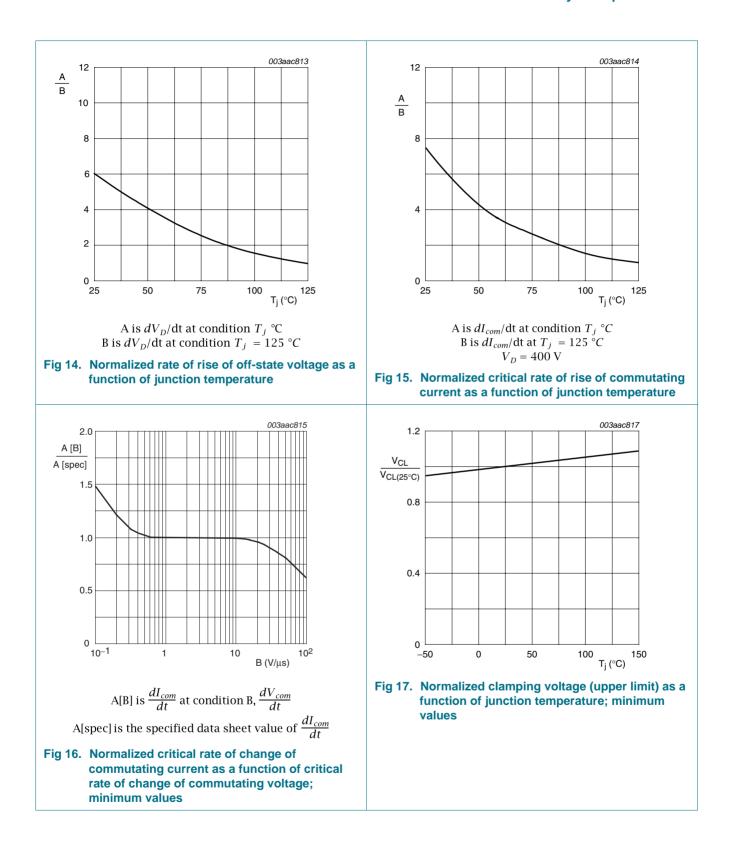


6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ I}_T = 100 \text{ mA}; \text{ LD+} \text{G-}; \text{ see } \frac{\text{Figure } 10}{10}$	1	-	10	mA
		$V_D = 12 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ I}_T = 100 \text{ mA}; \text{ LD- G-}$	1	-	10	mA
۱L	latching current	$V_D = 12 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ I}_G = 12 \text{ mA};$ see Figure 11	-	-	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; see <u>Figure 12</u>	-	9	25	mA
V _T	on-state voltage	I _T = 1.1 A; see <u>Figure 13</u>	-	-	1.3	V
V _{GT}	gate trigger voltage	I _T = 100 mA; V _D = 600 V; T _j ≤ 125 °C	0.15	-	-	V
		$I_T = 100 \text{ mA}; V_D = 600 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	V
I _D	off-state current	V _D = 600 V; T _j ≤ 125 °C	-	-	0.2	mA
		V _D = 600 V; T _j ≤ 25 °C	-	-	2	μA
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; gate open circuit; see <u>Figure 14</u>	1000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 1 \text{ A};$ $dV_{com}/dt = 15 \text{ V}/\mu s;$ gate open circuit; see Figure 15; see Figure 16	0.3	-	-	A/ms
V _{CL}	clamping voltage	I _{CL} = 100 mA; t _p = 1 ms; T _j ≤ 125 °C; see <u>Figure 17</u>	650	-	-	V



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7. Package outline

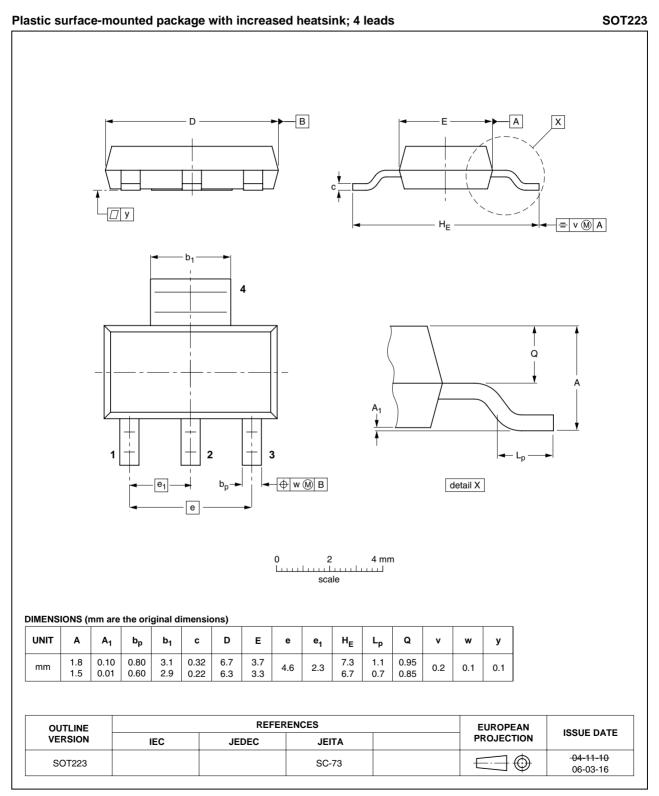


Fig 18. Package outline SOT223 (SC-73)

8. Revision history

Table 7. Revision hi	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
ACT108W-600E_2	20090526	Product data sheet	-	ACT108W-600E_1
Modifications:	 Table 6; dV 	/ _D /dt min data uprated		
ACT108W-600E_1	20090429	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions"

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